

## Appendices A

The following is the list of references for **Figure 1 (f)**.

- [S1] Du H, Liu Z, Xing W, et al. High-Performance AlN/GaN MISHEMTs on Si With In-Situ SiN Enhanced Ohmic Contacts for Mobile mm-Wave Front-End Applications. *IEEE Electron Device Letters*, 2023, 44, 6.
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